

MAR 0 2003

DOCKET NO.: 209291US0

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF:

:

Hiroyuki NAGASAWA et al

: GROUP: 1765

SERIAL NO.: 09/867,467

: EXAMINER: M. Song

FILED: May 31, 2001

:

RECEIVED

MAR 07 2003

FC 1700

FOR: METHOD OF MANUFACTURING SILICON CARBIDE,  
SILICON CARBIDE, COMPOSITE MATERIAL,  
AND SEMICONDUCTOR ELEMENT

**AMENDMENT**

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated December 4, 2002, please amend the above-identified application as follows.

**IN THE SPECIFICATION**

Please delete the last full paragraph on page 1 in favor of the following new paragraph:

-- Methods of manufacturing silicon carbide include reacting coke and silicon on a heated carbon surface and precipitating silicon carbide on a carbon surface (the Acheson method); heating and sublimating silicon carbide formed by the Acheson method and recrystallizing it (sublimation method, improved Lely method); the liquid deposition method in which silicon is melted in a carbon crucible and the suspended carbon and silicon are reacted in the crucible while drawing the product upward; and the like. --